Amendments to the Claims:

This listing of claims replaces all prior versions and listings of claims in the application:

Listing of Claims:

1. (Currently Amended) A display device comprising:

a pair of substrates;

an active matrix circuit and a driver circuit provided on one of the pair of **[[the]]** substrates; **[[and]]**

a sealing member formed so as to cover the driver circuit, the sealing member being capable of light blocking; and

an orientating film formed between the sealing member and the other one of the pair of substrates,

wherein the orientating film is in contact with the ~~on said~~ sealing member, and

wherein **[[said]]** the sealing member comprises a pigment for light blocking.

2. (Currently Amended) A display device according to claim 1,

wherein the active matrix circuit has pixels arranged in a matrix form, and

wherein regions in each of the pixels where source lines and **[[dram]]** drain lines overlap with a pixel electrode form a black matrix.

3. (Currently Amended) A display device according to claim 1,

wherein one of an electrode or a wiring line connected to a source or drain of a thin-film transistor formed in the active matrix circuit is one of a metal film, a semiconductor film, and a silicide film; and

wherein a light blocking film for the thin-film transistor is formed by using the one of the metal film, the semiconductor film, **[[0and]]** and the silicide film.

4. (Currently Amended) A display device according to claim 1, wherein said pair of **[[the]]** substrates are glass substrates or quartz substrates.

5. (Currently Amended) A display device according to claim 1 wherein said pair of **[[the]]** substrates are bonded to each other with the sealing member.

6. (Currently Amended) A device according to claim 1 further comprising:

at least a CMOS transistor formed in the driver circuit region, said CMOS transistor having an n-channel thin film transistor and a p-channel thin film transistor;

a thin film transistor formed in each pixel in the active matrix circuit, said thin film transistor having at least an active layer, a gate insulating film adjacent to said active layer, and a gate electrode adjacent to said gate insulating film,

wherein a light block film is formed over said gate electrode.

7. (Previously Presented) A device according to claim 1 further comprising a liquid crystal material interposed between the pair of substrates,

wherein said sealing member seals the liquid crystal material.

8. (Currently Amended) An electronic device comprising:

at least a first substrate and a second substrate;

a driver circuit region formed on said first substrate, said driver circuit region having at least one of a shift register circuit, a NAND circuit, a **[[lever]]** level shifter circuit and a buffer circuit;

an active matrix region formed on said first substrate, said active matrix region having at least a pixel;

a sealing member formed between said first and second substrates, said sealing member bonding said first and second substrates and covering said driver circuit region; and

an orientating film formed between said sealing member and said second substrate, wherein the orientating film is in contact with ~~on~~ said sealing member,

wherein said sealing member shields said driver circuit region from light; and

wherein said sealing member comprises a pigment for light blocking.

9. (Canceled)

10. (Previously Presented) A device according to claim 8 wherein said shift register circuit comprises at least a clocked inverter and an inverter.

11. (Previously Presented) A device according to claim 8 further comprising:

at least a CMOS transistor formed in said driver circuit region, said CMOS transistor having an n-channel thin film transistor and a p-channel thin film transistor;

a thin film transistor formed in said pixel, said thin film transistor having at least an active layer, a gate insulating film adjacent to said active layer, a gate electrode adjacent to said gate insulating film, and further comprising a light blocking film formed over said gate electrode.

12-14. (Canceled)

15. (Previously Presented) A device according to claim 8 further comprising a liquid crystal material injected between the first substrate and the second substrate.

16-21. (Canceled)

22. (Currently Amended) A display device comprising:

a pair of substrates;

an active matrix circuit and a driver circuit provided on one of the pair of **[[the]]** substrates;

a sealing member formed so as to cover the driver circuit, the sealing member being capable of light blocking; and

an orientating film formed between the sealing member and the other one of the pair of substrates, wherein the orientating film is in contact with the ~~on said~~ sealing member,

wherein the **[[said]]** sealing member comprises a pigment for light blocking; and

the **[[said]]** sealing member is not in contact with said one of the pair of **[[the]]** substrates.

23. (Previously Presented) A display device according to claim 22,

wherein the active matrix circuit has pixels arranged in a matrix form; and

regions in each of the pixels where source lines and drain lines overlap with a pixel electrode form a black matrix.

24. (Previously Presented) A display device according to claim 22,

wherein one of an electrode or a wiring line connected to a source or drain of a thin-film transistor formed in the active matrix circuit is one of a metal film, a semiconductor film, and a silicide film; and

wherein a light blocking film for the thin-film transistor is formed by using the one of the metal film, the semiconductor film, and the silicide film.

25. (Currently Amended) A display device according to claim 22 wherein said pair of **[[the]]** substrates are glass substrates or quartz substrates.

26. (Currently Amended) A display device according to claim 22 wherein said pair of **[[the]]** substrates are bonded to each other with the sealing member.

27. (Previously Presented) A device according to claim 22 further comprising:

at least a CMOS transistor formed in the driver circuit region, said CMOS transistor having an n-channel thin film transistor and a p-channel thin film transistor; and

a thin film transistor formed in each pixel in the active matrix circuit, said thin film transistor having at least an active layer, a gate insulating film adjacent to said active layer, a gate electrode adjacent to said gate insulating film,

wherein a light block film is formed over said gate electrode.

28. (Previously Presented) A device according to claim 22 further comprising a liquid crystal material interposed between the pair of substrates,

wherein said sealing member seals the liquid crystal material.

29. (Currently Amended) An electronic device comprising:

at least a first substrate and a second substrate;

a driver circuit region formed on said first substrate, said driver circuit region having at least one of a shift register circuit, a NAND circuit, a **[[lever]]** level shifter circuit and a buffer circuit;

an active matrix region formed on said first substrate, said active matrix region having at least a pixel;

a sealing member formed between said first and second substrates, said sealing member bonding said first and second substrates and covering said driver circuit region; and

an orientating film formed between said sealing member and said second substrate, wherein the orientating film is in contact with **[[on]]** said sealing member,

wherein said sealing member shields said driver circuit region from light;

said sealing member comprises a pigment for light blocking; and

said sealing member is not in contact with said ~~one of the pair of the substrates~~ first substrate.

30. (Previously Presented) A device according to claim 29 wherein said shift register circuit comprises at least a clocked inverter and an inverter.

31. (Previously Presented) A device according to claim 29 further comprising:

at least a CMOS transistor formed in said driver circuit region, said CMOS transistor having an n-channel thin film transistor and a p-channel thin film transistor; and

a thin film transistor formed in said pixel, said thin film transistor having at least an active layer, a gate insulating film adjacent to said active layer, a gate electrode adjacent to said gate insulating film, and further comprising a light blocking film formed over said gate electrode.

32. (Previously Presented) A device according to claim 29 further comprising a liquid crystal material injected between the first substrate and the second substrate.

33. (Previously Presented) A device according to claim 1 further comprising an interlayer insulating film made of a resin between said driver circuit and said sealing material.

34. (Previously Presented) A device according to claim 8 further comprising an interlayer insulating film made of a resin between said driver circuit and said sealing material.

35. (Canceled)

36. (Previously Presented) A device according to claim 22 further comprising an interlayer insulating film made of a resin between said driver circuit and said sealing material.

37. (Previously Presented) A device according to claim 29 further comprising an interlayer insulating film made of a resin between said driver circuit and said sealing material.